



Docket No.: R2180.0190/P190
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Takaaki Negoro et al.

Application No.: 10/780,699

Confirmation No.: 2014

Filed: February 19, 2004

Art Unit: 2814

For: Metal oxide silicon transistor and
semiconductor apparatus having high
lambda and beta performances

Examiner: P. X. Cao

AMENDMENT IN RESPONSE TO NON-FINAL OFFICE ACTION

MS Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

INTRODUCTORY COMMENTS

In response to the Office Action dated June 5, 2006, please amend the above-identified U.S. patent application as follows:

Amendments to the Claims are reflected in the listing of claims which begins on page 2 of this paper.

Remarks begin on page 8 of this paper.